

### **AMENDMENTS TO THE SPECIFICATION**

At page 1, please delete the section entitled "TECHNICAL FIELD" (lines 6-11), and replace with the following two sections:

#### **--CROSS-REFERENCE TO RELATED APPLICATIONS**

This application is the U.S. National Phase filing under 35 U.S.C. §371 of PCT/JP2004/013633, filed September 17, 2004, which designated the United States, which claims priority to Japanese Patent Application Nos. 2003-326146, filed September 18, 2003, 2003-331606, filed September 24, 2003, and 2004-119494, filed April 14, 2004. The contents of these applications incorporated herein by reference in their entireties.

#### **TECHNICAL FIELD**

The present invention relates to a positive resist composition and a method of forming a resist pattern--

At page 2, please delete the first paragraph (lines 1-5), and replace with the following paragraph:

--Chemically amplified positive resist compositions that have been proposed as ideal resist materials for methods in which exposure is conducted using a KrF excimer laser typically employ a polyhydroxystyrene-based resin, in which a portion of the hydroxyl groups have been protected with acid dissociable, dissolution inhibiting groups, as the base resin (see, for example, Japanese Unexamined Patent Application, First Publication No. Hei 4-211258)--.

At page 2, please delete the paragraph beginning at line 15 and ending at line 18, and replace with the following paragraph:

--An example of one such miniaturization technique that has been recently proposed is the thermal flow process, wherein a resist pattern is formed using normal lithography techniques, and the resist pattern is then subjected to heat treatment to reduce the pattern size (see, for

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example, Japanese Unexamined Patent Applications, First Publication Nos. 2000-188250 and 2000-356850)--.

Please delete the paragraph beginning at page 2, line 24, and ending at page 3, line 4.